

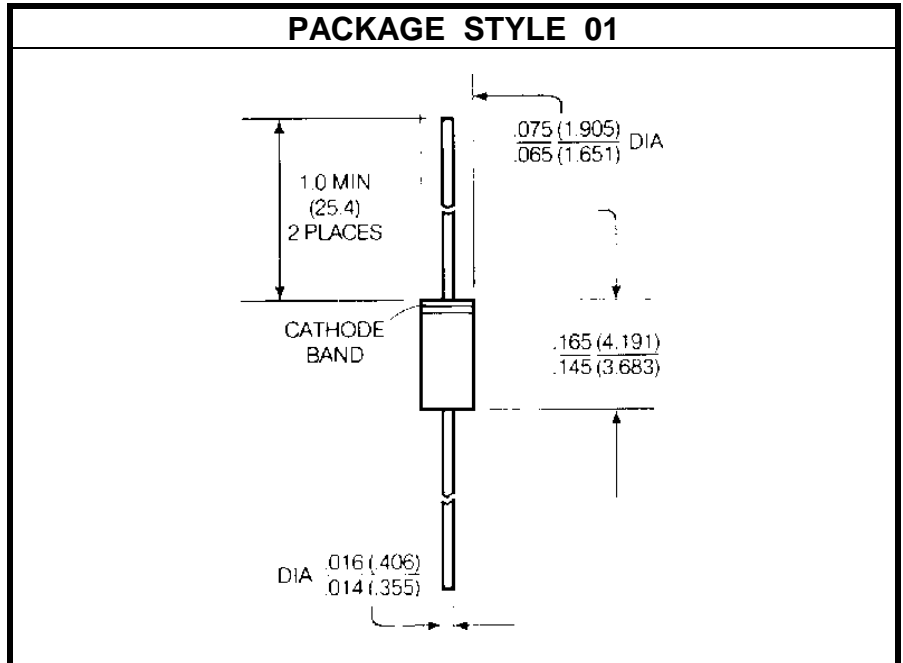
SILICON PIN DIODE CHIP

DESCRIPTION:

The **AP3000C-11** is a Passivated Epitaxial Silicon PIN Diode Housed in a Hermetically Sealed Glass Package. This Device is Designed to Cover a Wide Range of Control Applications Such as RF Switching, Phase Shifting, Modulation, Duplexing Limiting and Pulse Forming.

MAXIMUM RATINGS

| | |
|-------------------------|---------------------------------|
| I_F | 100 mA |
| V_R | 300 V |
| P_{DISS} | 250 mW @ T _A = 25 °C |
| θ_{JC} | 20 °C/W |



CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-----------------------|---|---------|-------------|---------|-------------|
| V_{BR} | I _R = 10 μA | 300 | | | V |
| C_J | V _R = 50 V V _R = 40 V | | f = 1.0 MHz | 0.2 | pF |
| R_S | I _F = 50 mA | | f = 100 MHz | 0.6 | Ohms |
| T_L | I _F = 10 mA I _R = 6.0 mA | | 1000 | | nS |
| T_{rr} | I _F = 20 mA I _R = 100 mA | | 100 | | nS |